

Giorgio Lulli

List of Publications by Year in descending order

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70
papers

1,045
citations

516710

16
h-index

454955

30
g-index

71
all docs

71
docs citations

71
times ranked

723
citing authors

#	ARTICLE	IF	CITATIONS
1	International Atomic Energy Agency intercomparison of ion beam analysis software. Nuclear Instruments & Methods in Physics Research B, 2007, 262, 281-303.	1.4	84
2	Radiation Enhanced Silicon Self-Diffusion and the Silicon Vacancy at High Temperatures. Physical Review Letters, 2003, 91, 245502.	7.8	71
3	Summary of "IAEA intercomparison of IBA software". Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1338-1342.	1.4	69
4	Solid-phase epitaxy of amorphous silicon induced by electron irradiation at room temperature. Physical Review B, 1987, 36, 8038-8042.	3.2	66
5	Ion implantation induced swelling in 6H-SiC. Applied Physics Letters, 1997, 70, 3425-3427.	3.3	62
6	Different methods for the determination of damage profiles in Si from RBS-channeling spectra: a comparison. Nuclear Instruments & Methods in Physics Research B, 1996, 118, 128-132.	1.4	57
7	Determination of He electronic energy loss in crystalline Si by Monte-Carlo simulation of Rutherford backscattering "channeling spectra. Nuclear Instruments & Methods in Physics Research B, 2000, 170, 1-9.	1.4	49
8	Influence of electron-beam parameters on the radiation-induced formation of graphitic onions. Ultramicroscopy, 1995, 60, 187-194.	1.9	42
9	Stopping and damage parameters for Monte Carlo simulation of MeV implants in crystalline Si. Journal of Applied Physics, 1997, 82, 5958-5964.	2.5	37
10	The Si surface yield as a calibration standard for RBS. Nuclear Instruments & Methods in Physics Research B, 2000, 161-163, 293-296.	1.4	28
11	Solid-phase epitaxy of implanted silicon at liquid nitrogen and room temperature induced by electron irradiation in the electron microscope. Philosophical Magazine Letters, 1990, 61, 101-106.	1.2	23
12	Low-energy recoils in crystalline silicon: Quantum simulations. Physical Review B, 2001, 63, .	3.2	21
13	On the Dynamic Annealing Mechanism in P+-Implanted Silicon. Physica Status Solidi A, 1986, 94, 95-106.	1.7	20
14	EPR and X-ray diffraction study of damage produced by implantation of B ions (50 keV, 1 MeV) or Si ions (50 keV, 700 keV, 1.5 MeV) into silicon. Nuclear Instruments & Methods in Physics Research B, 1995, 96, 215-218.	1.4	19
15	Monte Carlo simulation of ion implantation in crystalline SiC. Nuclear Instruments & Methods in Physics Research B, 1996, 120, 147-150.	1.4	18
16	Atomistic modeling of ion channeling in Si with point defects: "The role of lattice relaxation. Physical Review B, 2002, 66, .	3.2	18
17	Two-Dimensional Simulation of Undermask Penetration in 4H-SiC Implanted With Al^+ Ions. IEEE Transactions on Electron Devices, 2011, 58, 190-194.	3.0	17
18	Dose rate effects on the dynamic annealing mechanism in P+ -implanted silicon. Physica Status Solidi A, 1986, 97, 77-85.	1.7	16

#	ARTICLE	IF	CITATIONS
19	Comparison of results and models of solid-phase epitaxial growth of implanted Si layers induced by electron- and ion-beam irradiation. <i>Physical Review B</i> , 1993, 47, 14023-14031.	3.2	16
20	Vacancy effects in transient diffusion of Sb induced by ion implantation of Si ⁺ and As ⁺ ions. <i>Journal of Applied Physics</i> , 2000, 87, 8461-8466.	2.5	15
21	Channeling characterization of defects in silicon: an atomistic approach. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 230, 185-192.	1.4	15
22	Transmission Electron Microscopy of Self-Annealed Ion Implanted Silicon. <i>Japanese Journal of Applied Physics</i> , 1985, 24, L14-L16.	1.5	14
23	X-ray diffraction analysis of damage accumulation due to the nuclear energy loss of 50 keV and 1.2 MeV B ions implanted in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993, 80-81, 624-627.	1.4	14
24	MeV ion implantation induced damage in relaxed Si _{1-x} Ge _x . <i>Journal of Applied Physics</i> , 1997, 81, 2208-2218.	2.5	14
25	Binary collision approximation modeling of ion-induced damage effects in crystalline 6H-SiC. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1999, 148, 573-577.	1.4	14
26	Damage profiles in high-energy As implanted Si. <i>Journal of Applied Physics</i> , 2000, 88, 3993.	2.5	14
27	Stopping power of SiO ₂ for 0.2-3.0 MeV He ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2002, 196, 209-214.	1.4	13
28	Dynamic Monte Carlo simulation of nonlinear damage growth during ion implantation of crystalline silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1996, 112, 152-155.	1.4	12
29	Ab initio structures of As _n V _m complexes and the simulation of Rutherford backscattering channeling spectra in heavily As-doped crystalline silicon. <i>Physical Review B</i> , 2005, 72, .	3.2	12
30	Self annealing effects in P ⁺ implanted silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1987, 19-20, 475-479.	1.4	11
31	Interpretation of ion-channeling spectra in ion-implanted Si with models of structurally relaxed point defects and clusters. <i>Physical Review B</i> , 2004, 69, .	3.2	11
32	RBS-channeling determination of damage profiles in fully relaxed Si _{0.76} Ge _{0.24} implanted with 2 MeV Si ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1997, 122, 689-695.	1.4	10
33	Characterization of defects produced during self-annealing implantation of As in silicon. <i>Journal of Applied Physics</i> , 1990, 68, 2708-2712.	2.5	9
34	Atomistic simulation of ion channeling in heavily doped Si:As. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005, 230, 112-117.	1.4	8
35	Minority Carrier Lifetime in Furnace and E-Beam Annealed CZ Silicon. <i>Journal of the Electrochemical Society</i> , 1987, 134, 1239-1243.	2.9	7
36	Anomalous distribution of As during implantation in silicon under self-annealing conditions. <i>Journal of Applied Physics</i> , 1989, 66, 2940-2946.	2.5	7

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37	RBS-channeling analysis of virgin 6H- β -SiC: Experiments and Monte Carlo simulations. Nuclear Instruments & Methods in Physics Research B, 1998, 136-138, 1267-1271.	1.4	7
38	Structural characterization and modeling of damage accumulation in In implanted Si. Journal of Applied Physics, 2004, 95, 150-155.	2.5	7
39	Electron beam annealing of semiconductors by means of a specifically designed electron gun. Materials Chemistry and Physics, 1983, 9, 285-294.	4.0	6
40	Charge states distribution of 3350 keV He ions channeled in silicon. Nuclear Instruments & Methods in Physics Research B, 2002, 193, 113-117.	1.4	6
41	Ion-channeling analysis of As relocation in heavily doped Si:As irradiated with high-energy ions. Journal of Applied Physics, 2003, 94, 6215-6217.	2.5	6
42	Investigation of heavily damaged ion implanted Si by atomistic simulation of Rutherford backscattering channeling spectra. Nuclear Instruments & Methods in Physics Research B, 2005, 230, 613-618.	1.4	6
43	Defect-induced homogeneous amorphization of silicon: the role of defect structure and population. Journal of Physics Condensed Matter, 2006, 18, 2077-2088.	1.8	6
44	Ion implantation induced damage in relaxed Si _{0.75} Ge _{0.25} . Nuclear Instruments & Methods in Physics Research B, 1996, 112, 301-304.	1.4	5
45	Damage profiles in as-implanted silicon: fluence dependence. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 148-151.	1.4	5
46	Analysis of Aluminium Ion Implantation Damage into 6H-SiC Epilayers. Materials Science Forum, 1998, 264-268, 733-736.	0.3	5
47	The Monte Carlo Binary Collision Approximation Applied to the Simulation of the Ion Implantation Process in Single Crystal SiC: High Dose Effects. Materials Science Forum, 2001, 353-356, 599-602.	0.3	5
48	Electron spectroscopic imaging of dopant precipitation and segregation in silicon. Ultramicroscopy, 1991, 35, 265-269.	1.9	4
49	Computer simulation of ion channeling in Si containing structurally relaxed point defects. Nuclear Instruments & Methods in Physics Research B, 2003, 211, 50-54.	1.4	4
50	Germanium implanted Bragg gratings in silicon on insulator waveguides. Proceedings of SPIE, 2010, . .	0.8	4
51	2D Simulation of under-Mask Penetration in 4H-SiC Implanted with Al ⁺ Ions. Materials Science Forum, 0, 679-680, 421-424.	0.3	4
52	Comparison between electron beam and furnace rapid isothermal anneals of phosphorus implanted solar cells. Journal of Applied Physics, 1983, 54, 4127-4133.	2.5	3
53	Tailored emitter ion-implanted silicon solar cells. Solar Cells, 1984, 11, 69-85.	0.6	3
54	2 MeV Si ion implantation damage in relaxed Si _{1-x} Ge _x . Nuclear Instruments & Methods in Physics Research B, 1996, 120, 165-168.	1.4	3

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55	The minimum yield in channeling. Nuclear Instruments & Methods in Physics Research B, 2000, 164-165, 53-60.	1.4	3
56	Channeling energy loss of He ²⁺ in Si by transmission and back-scattering measurements: Experiments and computer modeling. Nuclear Instruments & Methods in Physics Research B, 2002, 193, 103-108.	1.4	3
57	Analysis of ion implanted silicon by RBS-channeling: influence of the damage model. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 232-235.	1.4	3
58	Low-energy silicon-on-insulator ion implanted gratings for optical wafer scale testing. Proceedings of SPIE, 2011, , .	0.8	3
59	Lifetime and crystal order in annealed CZ silicon. Physica Status Solidi A, 1988, 108, 503-508.	1.7	2
60	Damage and recovery in doped SOI layers after high energy implantation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 20-24.	3.5	2
61	Ion implantation of silicon at the nanometer scale. Journal of Applied Physics, 2007, 102, 074307.	2.5	2
62	e-beam-induced lateral seeded epitaxy of silicon on insulator. Materials Letters, 1986, 4, 185-188.	2.6	1
63	Radiation damage evolution and its relation with dopant distribution during self-annealing implantation of As in silicon. Journal of Materials Research, 1992, 7, 1413-1422.	2.6	1
64	Dynamics of void formation during implantation of Si under self-annealing conditions and their influence on dopant distribution. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 559-563.	1.4	1
65	Off-Axis Electron Holography of Nearly-Spherical Faceted Voids in Self-Annealed Implanted Silicon. Materials Characterization, 1999, 42, 241-247.	4.4	1
66	RBS-channeling analysis of ion-irradiation effects in heavily-doped Si:As. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 253-256.	1.4	1
67	Static Disorder in Si _{1-x} Ge _x Alloys and in Silicon on Insulator Structures. Materials Science Forum, 1996, 203, 217-222.	0.3	0
68	Electron holography study of voids in self-annealed implanted silicon. Philosophical Magazine Letters, 1998, 78, 445-451.	1.2	0
69	RADIATION INDUCED DEFECTS IN BIPOLAR POWER TRANSISTORS: INFLUENCE OF RADIATION ENERGY. , 2004, , .		0
70	RAPID ISOTHERMAL ANNEALING OF ION IMPLANTED SILICON DEVICES BY UNIFORM LARGE AREA IRRADIATION WITH A NEW ELECTRON BEAM SYSTEM. Journal De Physique Colloque, 1983, 44, C5-415-C5-419.	0.2	0